#### MARKING SCHEME SET 55/1/B

O No	SEI 55/1/B	Marilea	Total
Q. No.	Expected Answer / Value Points	Marks	Total Marks
			Warks
	Section A	l	
Set1,Q1	It is a measure of the sharpness of resonance.	1/2	
Set2,Q5			
Set3,Q2	Alternatively, $Q = \frac{1}{w_0 CR} / \frac{W_0 L}{R}$	1/2	
	No unit		1
Set1,Q2	To convert one form of energy into another.	1	
Set2,Q4	( <u>Alternatively</u> , To convert other forms of energy into electrical energy)		
Set3,Q5			1
Set1,Q3			
Set2,Q2	+Q		
Set3,Q4	Conducting surface	1	1
C-41 O4	M. P. A	1	1
Set1,Q4	Medium A	1	
Set2,Q3			1
Set3,Q1 Set1,Q5	Line A represents parallel combination,	1/2 + 1/2	1
Set1,Q3 Set2,Q1	Its slope is more(or It corresponds to a lower value of resistance)	72 + 72	
Set3,Q3	its slope is more(or it corresponds to a lower value of resistance)		1
5013,Q3	Section B		1 -
Set1,Q6			
Set2,Q7 Set3,Q10	Finding the angle of incidence 2		
Set5,Q10	It is the case of minimum deviation	1/2	
	$\sin i = \sin i$	1/2	
	$\mu = \frac{1}{\sin r} = \frac{1}{A}$	, 2	
	$\mu = \frac{\sin i}{\sin r} = \frac{\sin i}{\sin\left(\frac{A}{2}\right)}$		
	$\sqrt{3}$	1/2	
	$\Leftrightarrow \frac{1}{2} = \sin i$		
	$\Leftrightarrow \frac{\sqrt{3}}{2} = \sin i$ $\Leftrightarrow i = 60^{\circ}$	1/2	
	Alternatively,		
	Deviation produced by prism here is minimum.	1/2	
	$\sin\left(\frac{A+\delta_m}{a}\right)$		
	$\cdot u = \frac{\sin(-2)}{2}$		
	$\therefore \mu = \frac{\sin\left(\frac{A + \delta_m}{2}\right)}{\sin\frac{A}{2}}$		
	$\therefore \frac{\sqrt{3}}{2} = \sin\left(\frac{60 + \delta_m}{2}\right)$		
	$\Rightarrow 60^{\circ} \times 2 = 60^{\circ} + \delta_m$	1/	
	$\delta_m = 60^o$	1/2	

Page 1 of 17 Final Draft 18/03/15 01:00 p.m

Downloaded From: http://www.cbseportal.com

		I	1
	$A + \delta_m = i + e = 2i$	1/2	
	$\Rightarrow i = 60^{o}$	1/2	
	OR		2
	Finding the focal length Value of refractive index  1 ½ 1/2		_
	Lens maker's formula		
	$\frac{1}{f} = (\text{n-1}) \left( \frac{1}{R_1} - \frac{1}{R_2} \right)$	1/2	
	$\therefore \frac{1}{20} = (1.5-1) \left( \frac{1}{R_1} - \frac{1}{R_2} \right)$		
	$\therefore \frac{1}{R_1} - \frac{1}{R_2} = \frac{1}{10}$	1/2	
	$\therefore \frac{1}{f'} = \left(\frac{1.5}{1.65} - 1\right) \left(\frac{1}{10}\right)$		
	$f = -110 \ cm$ Refractive index of the medium should be 1.5 (i.e. same as that of material of lens)	1/2 1/2	
9.1.05			2
Set1,Q7 Set2,Q10 Set3,Q8	Determination of K.E  Wave length for ground state  Nature of change  1  1  1  1  1  1  1  1  1  1  1  1  1		
	In Ground state		
	$K.E = E_1 = 13.6eV = 2.18 \times 10^{-18} J$	1/2	
	$\lambda_1 = \frac{h}{\sqrt{2mK}} = 0.33$ nm	1	
	[ Note: Award $1\frac{1}{2}$ marks if student evaluates $\lambda_1$ directly without calculating $E_1$ ]  Alternatively,		
	$2\pi r_n = n\lambda_n$ $\therefore \lambda_{ground \ state} = 2\pi r_1 = 2\pi \times 0.53A^o$ $\cong 3.33 \ A^o \cong 0.33 \ nm$		
	In first excited state, the de Broglie wavelength will increase.	1/2	2
Set1,Q8 Set2,Q6 Set3,Q9	i) Finding the K.E & P.E in Ground state ii) Finding the K.E & P.E in Second excited state $\frac{1}{2} + \frac{1}{2}$		
	2 of 17 Einel Droft 19/02/	15 01.00	

Page 2 of 17 Final Draft 18/03/15 01:00 p.m

			1
	For Chave d state		
	For Ground state,		
	K.E = 13.6  eV (: $K.E = -T.E$ )	1/2	
	P.E = -27.2  eV (: $P.E = 2  T.E$ )	1/2	
	For second Excited state (n=3)		
	$K.E = -(-\frac{13.6}{9}) \text{ eV} = 1.51 \text{ eV}$	1/2	
	P.E = -3.02  eV	1/2	
	[ Award ½ mark if the student does the calculations by taking n=2 ]		2
Set1,Q9			
Set2,Q8 Set3,Q7	Distinguishing between sky wave and space wave mode 1 Reason 1		
	Space Wave Sky Wave		
	In space wave mode, the waves Reflected by Ionosphere	1	
	travel in straight line directly from transmitter to receiver	1	
	transmitter to receiver		
	Because frequencies is greater than 40 MHz penetrate the ionosphere.	1	
	(Alternatively: There frequencies (greater than 40 MHz) are not reflected by		
	the ionosphere)		2
Set1,Q10	01:0:11 :		
Set2,Q9	Shift in balance point for part 'a' and 'b' 1		
Set3,Q6	Reason 1		
	a) Balance Point will be shifted towards B.	1/2	
	The potential gradient will decrease and hence the balancing length will	1/2	
	increase.		
	b) No effect on balance point.	1/-	
	At balance point no current flows through resistor S.	1/2 1/2	2
	Section C	/2	<u> </u>
Set1,Q11			
Set1,Q11 Set2,Q20	Effect of dielectric on		
Set3,Q15	a) Electric field energy \frac{1}{2} +\frac{1}{2}		
	b) Charge \(\frac{1}{2} + \frac{1}{2}\)		
	c) Potential difference ½ +½		
	The capacitance of both the capacitors increases by a factor K.		
	a) New Electric field energy values are:	1/ . 1/	
	$= \frac{1}{2} K (C_1 V_1^2) \text{ and } \frac{1}{2} K (C_2 V_2^2)$	$\frac{1}{2} + \frac{1}{2}$	
	b) New charges are:		
		$\frac{1}{2} + \frac{1}{2}$	
	$= \frac{1}{2} KC_1 V_1 \text{ and } \frac{1}{2} KC_2 V_2$	/2 1 /2	
	<u> </u>	l	l

Page 3 of 17 Final Draft 18/03/15 01:00 p.m

	c) New P.Dvalues are: $ V_1 \text{ and } V_2 $ (The battery remains connected to the capacitors) $ \underline{ \text{Alternatively:} } \text{ The student may assumes that the battery has been removed.} $ a) New Electric field energy values are: $ = \frac{1}{2} \frac{Q^2}{KC_1} \text{ and } \frac{1}{2} \frac{Q^2}{KC_2} $ b) New charges are: $ Q \text{ and } Q \text{ as before} $ c) New P.D values are: $ \frac{Q}{KC_1} \text{ and } \frac{Q}{KC_2} $	$\frac{1}{2} + \frac{1}{2}$ $\frac{1}{2} + \frac{1}{2}$ $\frac{1}{2} + \frac{1}{2}$ $\frac{1}{2} + \frac{1}{2}$	
Set1,Q12 Set2,Q21 Set3,Q16	Definition of activity and SI unit  Calculation of half life +Activity  The rate at which the nuclei of the radioactive sample disintegrate.  [Alternatively, $R = \frac{-dN}{at}$ ]  SI Unit – becquerel $(Bq)$ / disintegration per second/  Half Life = 10 hrs.  (Given : Activity becomes half after 10 hrs.)  Activity after 20 hrs  (= 2× half life.)  = $\frac{1}{2^2} = \frac{1}{4}$ of intial activity  ∴ Intial activity  = $10000 \times 4$ dps  = $40000$ dps  Alternatively: $R = R_0 e^{-\lambda t}$	1/2 1/2 1/2 1/2 1/2	3
	$10,000 = R_0 e^{-\lambda \times 20}$ $5000 = R_0 e^{-\lambda \times 30}$ By dividing $2 = e^{\lambda \times 10}$		

Page 4 of 17 Final Draft 18/03/15 01:00 p.m

		1	
	$\log 2 = 10\lambda$ $= \frac{\log 2}{T_{\frac{1}{2}}} \times 10$		
	$T_{\frac{1}{2}} = 10 \ hour$		
	Initial activity = $10000 \times (2)^2 = 40000$ dps	1/2	3
Set1,Q13 Set2,Q22 Set3,Q17	Answers of part (a), (b), (c) 1+1+1		
	(a) The intensity of inteferance fringes in double slit arrangement is modulated by the diffraction pattern of each slit.  Alternatively, In double slit experiment the interference pattern on the screen is actually supermodition of single slit diffraction for each slit.	1	
	<ul> <li>is actually superposition of single slit diffraction for each slit.</li> <li>(b) Waves diffracted from the edges of the circular obstacle interfere constructively at the centre of the shadow producing a bright spot.</li> </ul>	1 1/2	
	(c) Resolving power = $\frac{2\mu Sin\theta}{1.22\lambda}$ $\therefore$ Resolving power is inversely proportional to wavelength and directly proportional to the refractive index.	1/2	
	Alternatively:  (i) $R.P \propto \frac{1}{\lambda}$ (ii) $R.P \propto \mu$		3
Set1,Q14 Set2,Q16 Set3,Q18	Definition of Intensity of radiation 1 Calculation of work function 1 ½ Response to red light ½		
	Definition: It is defined as the number of photons (of given frequency)incident per unit area per unit time.	1	
	[Alternatively, $I = nhv$ )		
	$\frac{hc}{\lambda} = \varphi_o + eV_o$	1/2	
	$\varphi_o = \left(\frac{6.6 \times 10^{-34} \times 3 \times 10^8}{2270 \times 10^{-10} \times 1.6 \times 10^{-19}} - 1.3\right) \text{eV}$	1/2	
	= 4.2 eV (also accept the answer in joules)	1/2	
	For red light incident photon energy will be less than the work function, hence no emission of electrons.(Also accept : There would be no photoemission)	1/2	3

Page 5 of 17 Final Draft 18/03/15 01:00 p.m

	OR		
	Photo electric equation 1 Explanation of observations (any two) 1+1		
	Incident photon energy(hv) is used up in two ways:  (1) A part of this energy is used to remove the electrons.  (2) Remaining part of the energy imparts KE to the emitted electrons	1/2	
	$h\nu = \phi_o + (K.E)$		
	$hv - \phi_o = \frac{1}{2}mv^2 = eV_o$	1/2	
	Explanation: (i)Maximum KE depends on frequency and not on intensity. (ii) There exists a threashold frequency $v_0$ (for which $hv_0 = \phi_0$ ) below which no photoemission takes place.		
	(iii)Basic elementary process involved is absorption of photon by e. This process is instantaneous.  (Any Two)	1+1	3
Set1,Q15 Set2,Q17	Answers of parts (a), (b) & (c) 1+1+1		
Set3,Q11	a) Microwaves	1	
	b) Electric charges can acquire energy and momentum from e.m. waves.	1	
	c) $U = U_E + U_B = \frac{1}{2} \epsilon_0 E^2 + \frac{B^2}{2\mu_0}$	1/2 + 1/2	3
Set1,Q16 Set2,Q18 Set3,Q12	Drawing of magnetic field lines $1+1$ Explanation $\frac{1}{2} + \frac{1}{2}$		
		1+1	
	Explanation: For diamagnetic material resultant magnetic moment in an atom is zero. In presence of external magnetic field, they acquire a net magnetic moment in a direction opposite to applied field. (or get repellled)	1/2	
	In paramagnetic material there is a permanent magnetic dipole moment of atoms. The external magnetic field tends to align these along its own direction. (or attracts them).	1/2	3
Set1,Q17 Set2,Q19 Set3,Q13	Explanation of two processes with diagram $1+1$ Definition of depletion region & barrier potential $\frac{1}{2} + \frac{1}{2}$		

Page 6 of 17 Final Draft 18/03/15 01:00 p.m

	Two important processes involved during the formation of p-n jumction are  (i) Diffusion  (ii) Drift	1/2 + 1/2	
	<u>Diffusion</u> is the movement of the majority charge carriers across the junction. <u>Alternatively</u> , Diffusion results in the formation of negative and positive space charge regions around the junction	1/2	
	<u>Drift</u> is the movement of the minority charge carriers across the junction. $W = 0000$ $0000$ $0000$ $0000$ $0000$ $0000$ $0000$ $0000$ $0000$ $0000$ $0000$	1/2	
	Alternatively, $v_{\circ}$		
	Depletion Region: The <u>depletion layer</u> is the negative and positive space charge region formed around the junction. <u>Alternatively</u> : Depletion region: Space Charge region on either side of the junction together is known as depletion region.	1/2	
	Barrier Potential: The loss of electron from n region and gain of electron by p region causes a difference of potential across the junction. This is known as barrier potential.  Alternatively: The potential developed across the junction, that opposes the flow of (majority) charge carriers.	1/2	3
Set1,Q18 Set2,Q11 Set3,Q14	i) Fabrication ½ ii) Working 1½ iii) Advantage ½ +½		
	LED is fabricated by:  (i) Heavy doping of both th p and n regions.  (ii) providing a transparent cover so that light can come out.  (Any one point)	1/2	
	<b>Working:</b> When the diode is forward biased electrons are sent from $n \to p$ and holes from $p \to n$ . At the junction boundary, the excess minority carriers on either side of junction recombine with majority carriers.	1/ <sub>2</sub> + 1/ <sub>2</sub> + +	
	5 7 of 17 Final Draft 19/02/	15 01.00	

Page 7 of 17 Final Draft 18/03/15 01:00 p.m

	This releases energy in the form of photon $hv = Eg$ .	1/2	
	Advantages (any two) Low operational voltage Long life	1/2 + 1/2	
	Fast on /off switching capability No warm up time required		3
Set1,Q19 Set2,Q12 Set3,Q21			
	[Full credit for this part maybe given to the student. ]		
	$A_c = 12V$	2	
	$\mu = \frac{A_m}{A_c} = \frac{75}{100} = 0.75$	1/2	
	$A_m = 0.75 \times 12 = 9 \text{ V}$	1/2	3
Set1,Q20 Set2,Q13 Set3,Q22	a) Explanation of the phenomenon using diagram b) Explanation of polarisation of Reflected light. Derivation of Brewster's Law  1½  1½		
	Incident Sunlight (Unpolarised)  Scattered Light (Polarised)  To Observer	1/2	
	The basic phenomenon / process which occurs is polarisation.	1/2	
	The incident unpolarised sun ligh encounte the molecules of earth's atmosphere. Under the influence of electric field of incident wave the $e^-$ in the molecule acquires component of motion in both these direction. If an observer is looking $90^0$ to the direction of the Sun ,charge accelarating parallel to double arrow do not radiate energy towards the observer.[Their accelaration has no transverse component.] This explain polarisation of scattered light from sky.	1/2	
	Incident Reflected  AIR  Refracted  MEDIUM	1/2	

Page 8 of 17 Final Draft 18/03/15 01:00 p.m

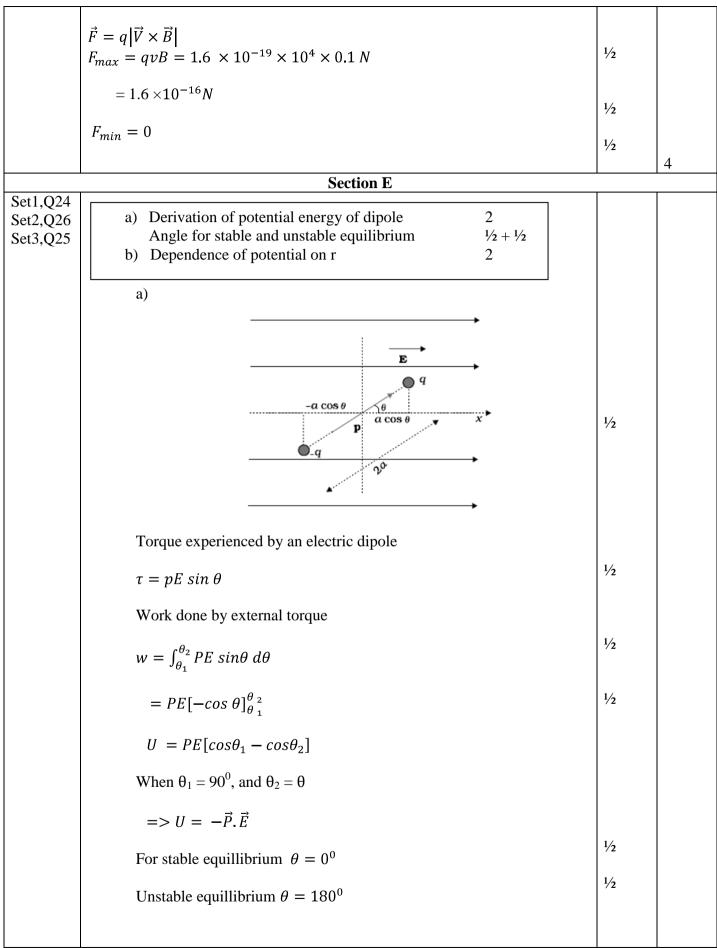
	When unpolarised light is incident at polarising angle, at the interface of a refracting medium, the reflected ray being perpendicular to the refracted ray is completely polarised.		
	Now $\mu = \frac{\sin i}{\sin r}$ $\therefore \mu = \frac{\sin i_p}{\sin (90 - i_p)}  (\because i_p + r = 90^o)$	1/2	
	$\sin(90 - i_p)$ $\therefore \mu = \tan i_p$	72	
	This is Brewter's Law	1/2	3
Set1,Q21 Set2,Q14 Set3,Q19	i) Derivation of the Average power in inductor $1\frac{1}{2}$ ii) Ratio of Power factors $P_1$ and $P_2$ $1\frac{1}{2}$		
	For an ideal inductor connected to ac source		
	$V = V_0 \sin \omega t \qquad I = I_0 \sin \left(\omega t - \frac{\pi}{2}\right)$	1/2	
	$P_{avg} = \frac{1}{T} \int_{0}^{T} V_0 I_0 \sin \omega t \cos \omega t  dt$	1/2	
	$=\frac{1}{T}\frac{V_0I_0}{2}\int_o^T\sin 2\omega t\ dt$		
	$= \frac{1}{T} \frac{V_0 I_0}{2} \left[ \frac{\cos 2\omega t}{2\omega} \right]_0^T = 0$	1/2	
	(Also accept any other correct method)		
	Power factor $\cos \emptyset = R/Z$	1/2	
	For LR circuit, at $X_L = R$		
	$Z = \sqrt{R^2 + R^2}$		
	$Z = R\sqrt{2}$		
	$P_1 = \cos\phi = \frac{R}{R\sqrt{2}} = \frac{1}{\sqrt{2}}$	1/2	
	For LCR circuit $X_L = X_C$		
	$Z = \sqrt{R^2} = R$		

Page 9 of 17

Final Draft 18/03/15 01:00 p.m

	l R	1	
	Power factor $P_2 = \frac{R}{R} = 1$		
	$=>\frac{P_1}{P_2}=1:\sqrt{2}$		
	1	1/2	
	[Award 1½mark if the student writes directly : $P_1 = \frac{1}{\sqrt{2}}$ and $P_2 = 1$		
	$\left  \therefore \frac{P_1}{P_2} = \frac{1}{\sqrt{2}} \right]$		3
Set1,Q22	Definition of resistivity 1		
Set2,Q15 Set3,Q20	Graphs 1/2 +1/2		
5013, Q20	Explanation $\frac{1}{2} + \frac{1}{2}$		
	Resistivity of a conductor is defined as the resistance of a material (of a Conductor) of unit length and unit area of cross section.	1	
	(Alternatively, $\rho = \frac{RA}{l}$ )		
	(Externatives), p		
	<b>1</b>		
	Resistivity $\rho$ (10 $^{8}\Omega$ m) $\rho$ (0.2)		
	(10)		
		$\frac{1}{2} + \frac{1}{2}$	
	stiv.		
	gesi.		
	0 50 100 150		
	Temperature $T(K) \rightarrow T$		
	Conductor Semiconductor		
	In conductor with increase in temperatures relaxtion time decreases, but	1/2	
	number density of charge carriers is not dependent on temperature. Hence,	, 2	
	ho increases.		
	In semiconductors number density of charge carriers increases with	1/2	
	temperature, it dominates the decrease in relaxtion time. Hence, $\rho$	/ 2	
	decreases.		
	Section D		3
Set1,Q23	Section D		
Set2,Q23	Values displayed 2		
Set3,Q23	Answer of part (b)  \frac{1}{2}  \text{Maximum & Minimum force}  \text{1 +\frac{1}{2}}  \text{1}		
	Wiaximum & Minimum force 1 +72		
	a) Asha and her family helpful, concern for others, caring nature (any two)	1	
	Doctor was generous, helping nature, caring (any two)	1	
	(Any other alternative correct value should be accepted)		
	b) High magnetic field required. / (Expensive set up needed) Any other	1/2	
	correct answer		
Dog	[Note: Full credit of ½ mark may be given [for this part to all students] to 10 of 17 Final Draft 18/03/	/15 01:00	n m

Page 10 of 17 Final Draft 18/03/15 01:00 p.m



Page 11 of 17 Final Draft 18/03/15 01:00 p.m

(b) $V_p = V_q + V_q + V_{-2q}$		
$= \frac{kq}{r-a} + \frac{kq}{r+a} - \frac{2kq}{r}$	1/2	
$= kq\left(\frac{r+a+r-a}{r^2-a^2}\right) - \frac{2kq}{r}$		
$=\frac{2kqr}{r^2-a^2}-\frac{2kq}{r}$		
$=2kq\left[\frac{r}{r^2-a^2}-\frac{1}{r}\right]$	1/2	
$= 2kq \left[ \frac{r^2 - r^2 + a^2}{r(r^2 - a^2)} \right] = \frac{2kqa^2}{r(r^2 - a^2)}$	1/2	
For r>> a		
$V_p = \frac{2kqa^2}{r^3}$		
$V_p \propto \frac{1}{r^3}$	1/2	5
OR		
a) Electric flux and its SI unit b) Calculation of Electric flux c) Derivation of electric field due to infinite plane sheet $ \begin{array}{ccc} 1 + \frac{1}{2} \\ 1 \\ 2 \frac{1}{2} \end{array} $		
a) Electric flux equals the surface integral of electric field over the given surface.	1	
$(\underline{\mathbf{Alternatively}}, \ \phi_E = \int \vec{E} \cdot \overrightarrow{ds})$		
S.I Unit $Nm^2/C$ (Alternatively: V-m)	1/2	
b) By Gauss's Law		
$\oint \vec{E} \cdot \overrightarrow{ds} = \frac{q}{\epsilon_0}  (q = \text{charge enclosed})$	1/2	
Here the charge enclosed in the cube = q		
$\therefore \phi_E = \oint \vec{E} \cdot \overrightarrow{ds} = \frac{q}{\epsilon_0}$	1/2	

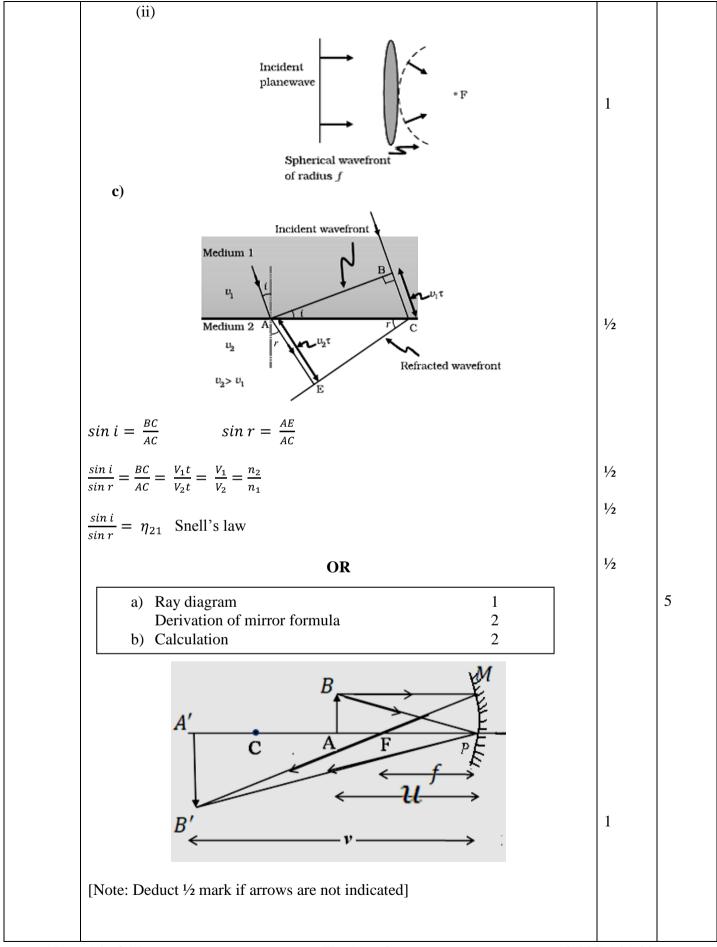
Page 12 of 17

Final Draft

18/03/15 01:00 p.m

	Surface charge density $\sigma$ $x \rightarrow \mathbb{R}$	1/2	
	$\phi = \oint \vec{E} \cdot \overrightarrow{ds} = \int_{s1} \vec{E} \cdot \overrightarrow{ds} + \int_{s2} \vec{E} \cdot \overrightarrow{ds} + \int_{s3} \vec{E} \cdot \overrightarrow{ds}$	1/2	
	= EA + EA + 0 = 2EA	1	
	By Gauss Law,		
	$2 E A = \frac{q}{\epsilon_0}$	1/2	
	$\therefore E = \frac{q}{2\epsilon_0} = \frac{\sigma A}{2\epsilon_0 A} = \frac{\sigma}{2\epsilon_0}$	1/2	
	∴ E is independent of x		5
Set1,Q25 Set2,Q24 Set3,Q26	a) Definition of wave front b) Diagram of wave fronts for (i) Reflection of plane wave by concave mirror (ii) Refraction of plane wave by convex lens c) Verification of Snell's Law/  a) Locus of all the points which are in same phase / surface of constant phase b) (i)  Concave mirror of radius R  Incident planewave  Spherical wavefront of radius R/2	1	

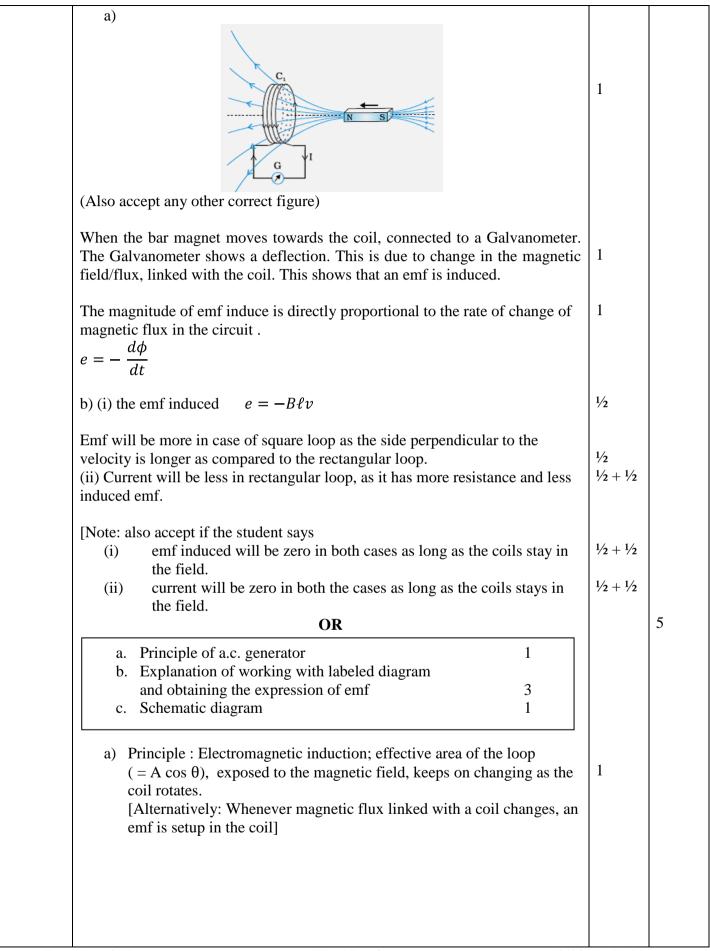
Page 13 of 17 Final Draft 18/03/15 01:00 p.m



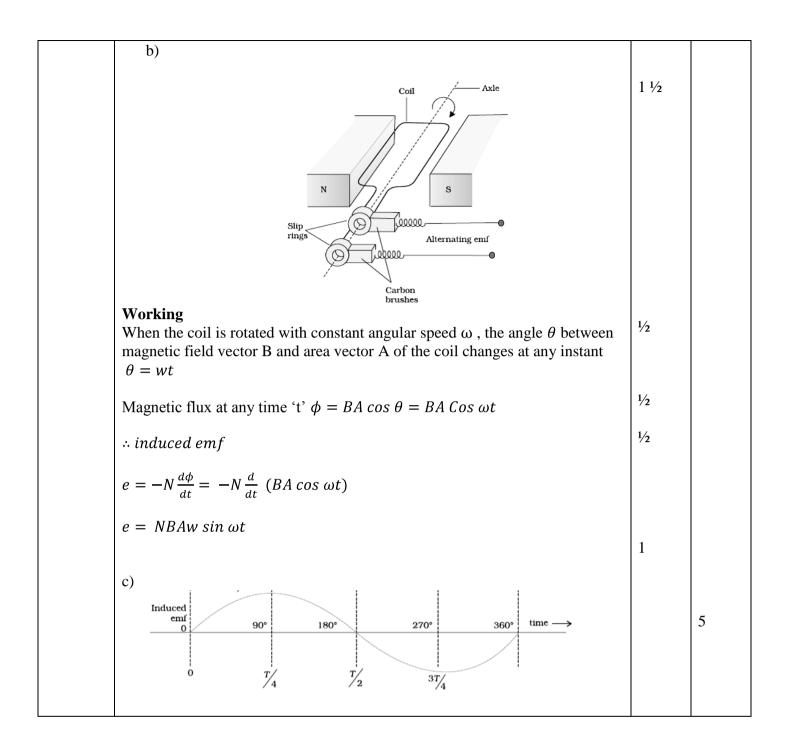
Page 14 of 17 Final Draft 18/03/15 01:00 p.m

	In $\triangle ABP$ and $\triangle A'B'P$		
	$\frac{AB}{A'B'} = \frac{AP}{A'P}$	1/2	
	In $\triangle MPF$ and $\triangle B'A'F$		
	$\frac{MP}{A'B'} = \frac{FP}{A'F}$		
	But $AB = MP$		
	$\therefore \frac{AP}{A'P} = \frac{FP}{A'P} = \frac{FP}{A'P-FP}$	1/2	
	$\frac{-u}{-v} = \frac{-f}{-(v-f)}$		
	uv - uf = vf	1/2	
	Dividing by <i>uvf</i>		
	$\frac{1}{f} - \frac{1}{v} = \frac{1}{u}$		
	$\frac{1}{v} + \frac{1}{u} = \frac{1}{f}$	1/2	
	b) Here the object is virtual and image is real $u = +12$ cm		
	(i)		
	$\frac{1}{v} - \frac{1}{u} = \frac{1}{f} = \frac{1}{v} - \frac{1}{+12} = \frac{1}{20}$	1/2	
	=> v = 7.5 cm from the lens	1/2	
	(ii)		
	$\frac{1}{v} - \frac{1}{u} = \frac{1}{f}$		
	$=>\frac{1}{v}-\frac{1}{12}=\frac{1}{-16}$	1/2	
	$=> v = 48 \ cm$ from the lens	1/2	5
Set1,Q26 Set2,Q25 Set3,Q24	a) Description with diagram  Statement of Faraday's law  b) Answers and their justification  parts (i) & (ii)  1+1		J
	2.15 of 17 Final Duaft 19/02	(15.01.00	

Page 15 of 17 Final Draft 18/03/15 01:00 p.m



Page 16 of 17 Final Draft 18/03/15 01:00 p.m



Page 17 of 17 Final Draft 18/03/15 01:00 p.m